

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1 – 47 (Cancelled)

48. (Currently Amended) A method comprising:

forming insulating spacers adjacent to sidewalls of a gate by forming an insulating layer and removing a portion of the insulating layer that is not on the sidewalls including performing a combination of a dry etch and then a wet etch; ~~[[and]]~~

forming extension regions after forming the insulating spacers by ion implantation using the insulating spacers as a mask; and

forming a source and a drain by ion implantation,

wherein the extension regions are shallower than the source and the drain, and

wherein the source and the drain are more heavily doped than the extension regions.

49. (Currently Amended) The method of claim 48, further comprising:

removing the insulating spacers by performing a wet etch; and

after said removing the insulating spacers, performing said forming ~~[[a]]~~ the source and ~~[[a]]~~ the drain ~~[[by ion implantation]]~~.

50. (Withdrawn) The method of claim 48, wherein said forming the insulating spacers comprises forming insulating spacers that each include a metal oxide.

51. (Previously Presented) The method of claim 48, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 10-200 Angstroms.
52. (Previously Presented) The method of claim 51, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 20-100 Angstroms.
53. (Currently Amended) A method comprising:
- forming insulating spacers adjacent to sidewalls of a gate by depositing an insulating layer at a temperature that is higher than 750°C and anisotropically etching the insulating layer; [[and]]
- forming extension regions after forming the insulating spacers by ion implantation using the insulating spacers as a mask; and
- forming a source and a drain by ion implantation,
- wherein the extension regions are shallower than the source and the drain, and
- wherein the source and the drain are more heavily doped than the extension regions.
54. (Previously Presented) The method of claim 53, wherein said depositing the insulating layer comprises depositing the insulating layer by low pressure chemical vapor deposition.
55. (Currently Amended) The method of claim 53, further comprising:
- removing the insulating spacers by performing a wet etch; and

after said removing the insulating spacers, performing said forming [[a]] the source and [[a]] the drain [[by ion implantation]].

56. (Previously Presented) The method of claim 53, wherein said anisotropically etching the insulating spacers comprises performing a combination of a dry etch and then a wet etch.
57. (Withdrawn) The method of claim 53, wherein said forming the insulating spacers comprises forming insulating spacers that each include a metal oxide.
58. (Withdrawn) The method of claim 53, wherein said forming the insulating spacers comprises forming insulating spacers that each include an organic material.
59. (Previously Presented) The method of claim 53, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 10-200 Angstroms.
60. (Previously Presented) The method of claim 53, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 20-100 Angstroms.
61. (Currently Amended) A method comprising:

forming insulating spacers adjacent to sidewalls of a gate;

forming extension regions after forming the insulating spacers by ion implantation using the insulating spacers as a mask;

removing the insulating spacers by etching; and

forming a source and a drain by ion implantation,

wherein the extension regions are shallower than the source and the drain, and

wherein the source and the drain are more heavily doped than the extension regions.

62. (Previously Presented) The method of claim 61, wherein said removing the insulating spacers comprises performing a wet etch.
63. (Previously Presented) The method of claim 61, wherein said forming the insulating spacers comprises growing an insulating layer over the gate by oxidation and removing a portion of the insulating layer that is not on the sidewalls.
64. (Previously Presented) The method of claim 61, wherein said forming the insulating spacers comprises depositing an insulating layer at a temperature that is higher than 750°C and removing a portion of the insulating layer.
65. (Previously Presented) The method of claim 61, wherein said forming the insulating spacers comprises depositing an insulating layer and removing a portion of the insulating layer by performing a combination of a dry etch and then a wet etch.
66. (Withdrawn) The method of claim 61, wherein said forming the insulating spacers comprises forming insulating spacers that each include a metal oxide.
67. (Withdrawn) The method of claim 61, wherein said forming the insulating spacers comprises forming insulating spacers that each include an organic material.
68. (Previously Presented) The method of claim 61, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 10-200 Angstroms.

69. (Previously Presented) The method of claim 68, wherein said forming the insulating spacers comprises forming insulating spacers that each have a thickness in a range between 20-100 Angstroms.